

Dual N-Ch 30V Fast Switching MOSFETs

General Description

The UM3214 is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The UM3214 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	A
I_{DM}	Pulsed Drain Current ²	36	A
EAS	Single Pulse Avalanche Energy ³	53	mJ
I_{AS}	Avalanche Current	22	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	25	$^{\circ}C/W$

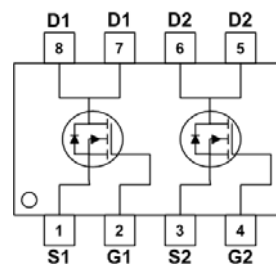
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
30V	12m Ω	9A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

Dual SOP8 Pin Configuration



Dual N-Ch 30V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.023	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$	---	10	12	m Ω
		$V_{GS}=4.5V, I_D=6A$	---	15	18	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.08	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=8A$	---	24	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.8	3	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=8A$	---	9.63	13.5	nC
Q_{gs}	Gate-Source Charge		---	3.88	5.4	
Q_{gd}	Gate-Drain Charge		---	3.44	4.8	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=1.5\Omega, I_D=8A$	---	4.2	8.4	ns
T_r	Rise Time		---	8.2	15	
$T_{d(off)}$	Turn-Off Delay Time		---	31	62	
T_f	Fall Time		---	4	8	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	940	1316	pF
C_{oss}	Output Capacitance		---	131	183	
C_{rss}	Reverse Transfer Capacitance		---	109	153	

Guaranteed Avalanche Characteristics

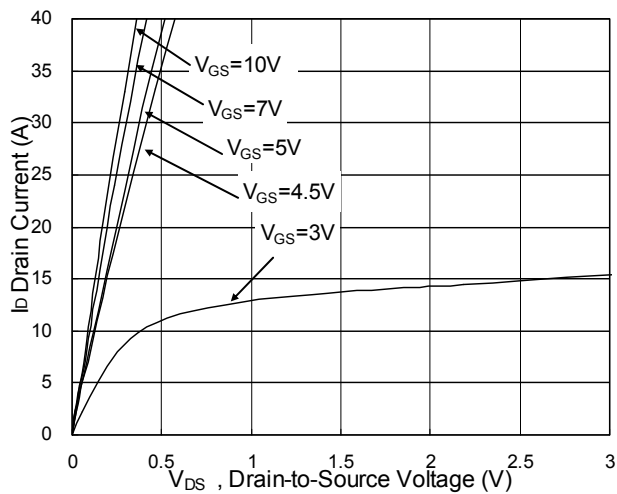
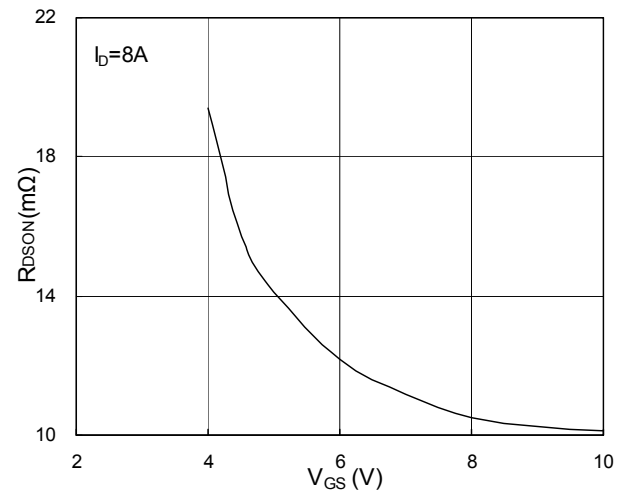
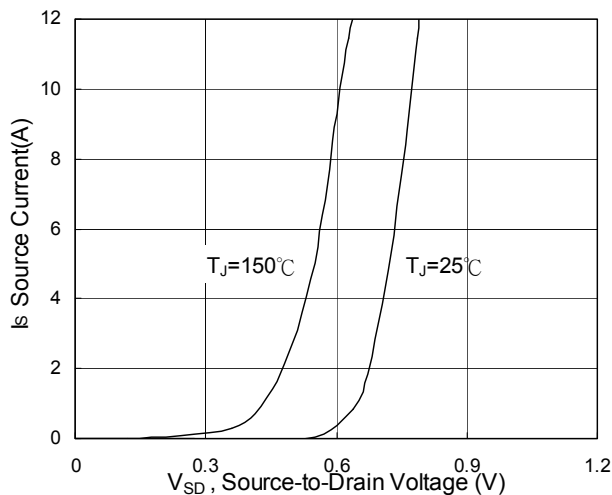
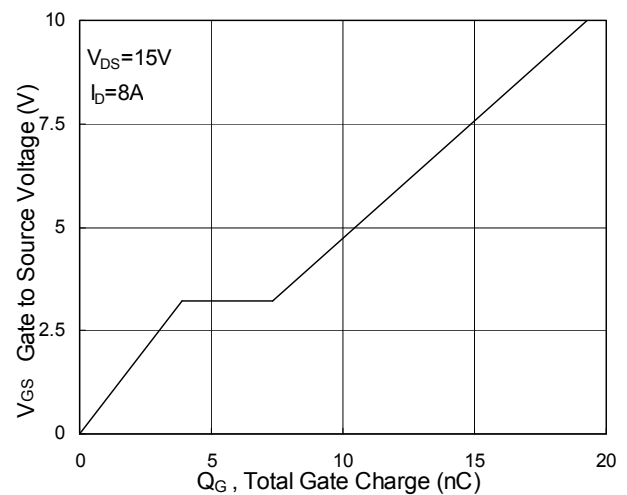
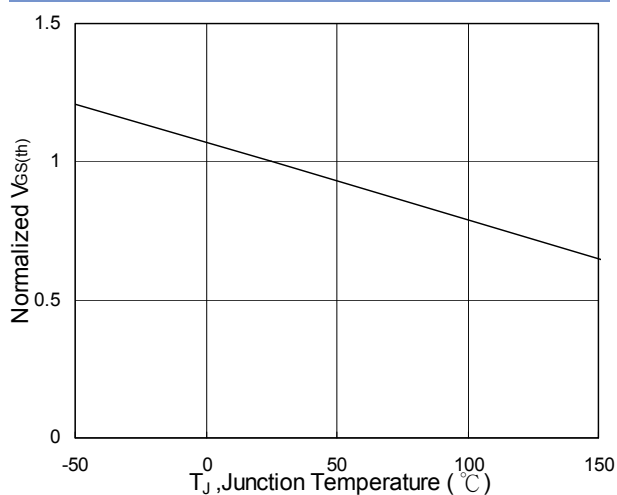
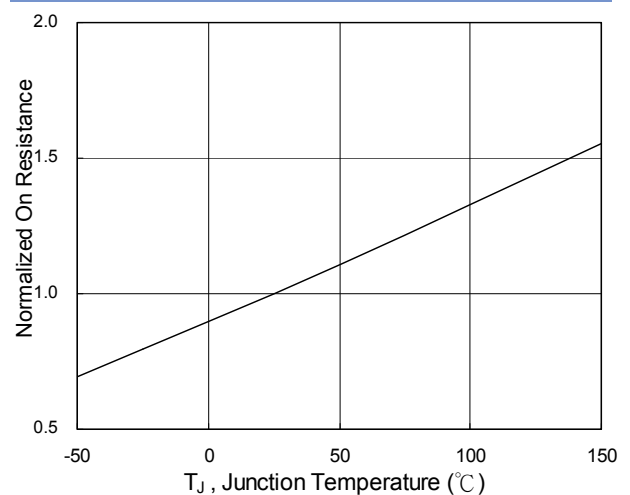
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	$V_{DD}=25V, L=0.1\text{mH}, I_{AS}=15A$	24.6	---	---	mJ

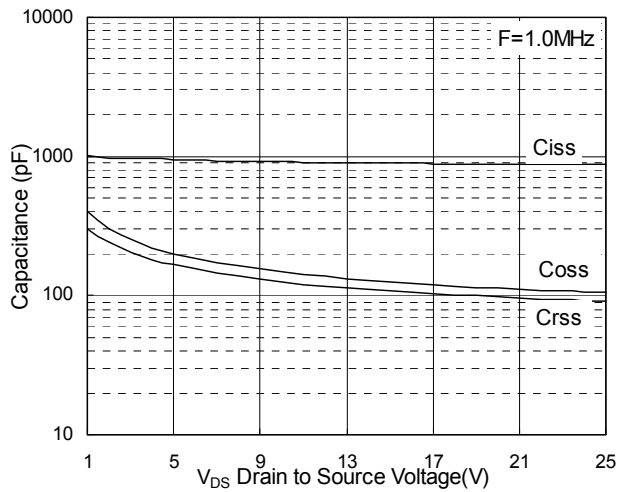
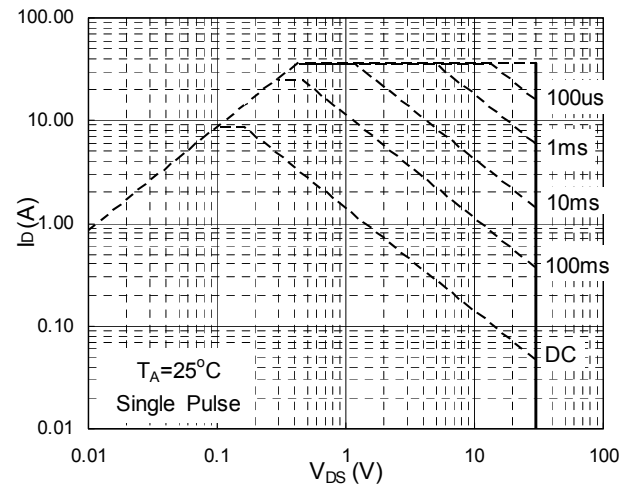
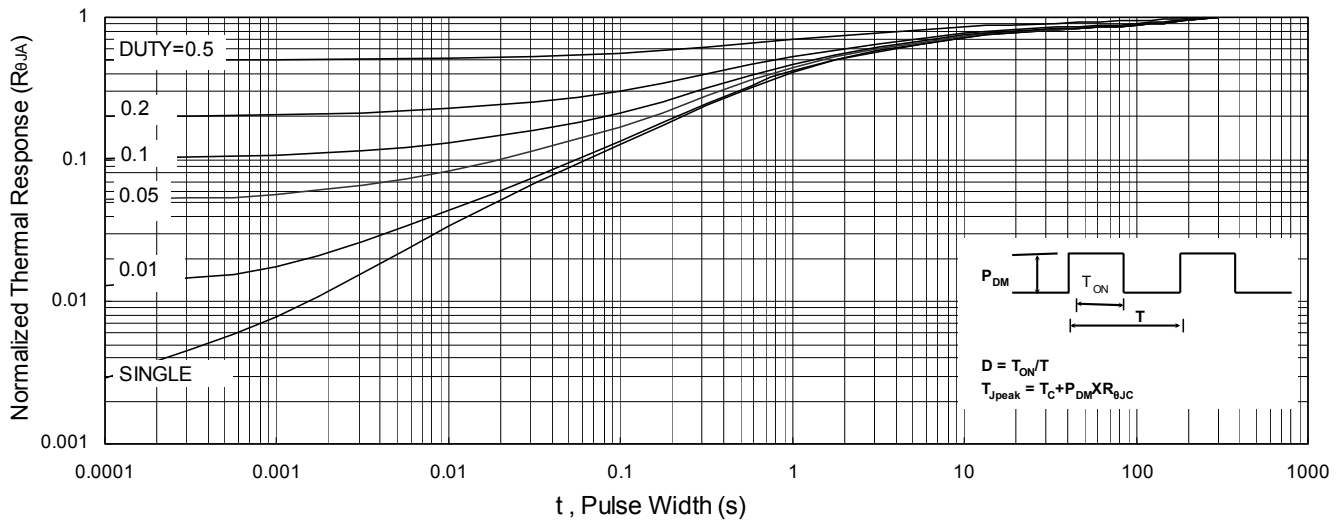
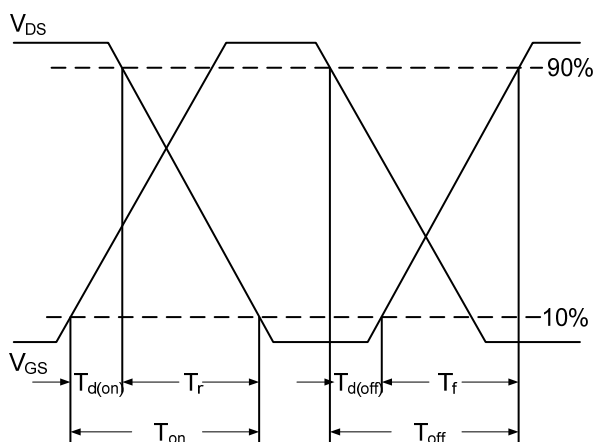
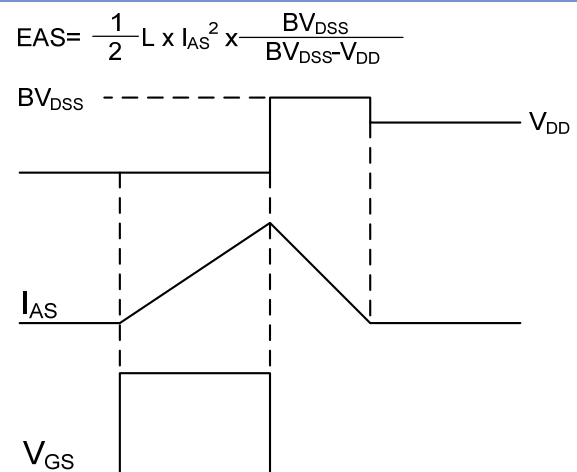
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	9	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	36	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=8A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	8	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=22A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Characteristics

Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs. G-S Voltage

Fig.3 Forward Characteristics of Reverse

Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform